

isc Silicon NPN Power Transistor

BDY98

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
- : V_{CEO(SUS)} = 250V(Min)
- Low Collector-Emitter Saturation Voltage-
- : V_{CE(sat)} = 1.5V(Max.) @ I_C= 2.5A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

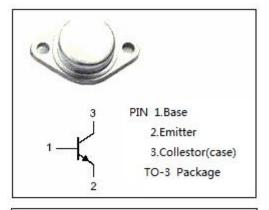
• Designed for use in switching regulators applications.

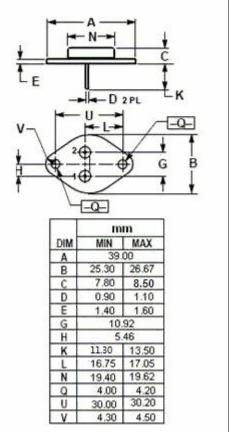
| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|------|
| Vсво | Collector-Base Voltage | 400 | V |
| V _{CEO} | Collector-Emitter Voltage | 250 | V |
| V _{EBO} | Emitter-Base Voltage | 7 | V |
| lc | Collector Current-Continuous | 10 | А |
| I _{CM} | Collector Current-Peak | 15 | А |
| Pc | Collector Power Dissipation @ T_c =90 °C | 40 | W |
| TJ | Junction Temperature | ire 150 | |
| T _{stg} | Storage Temperature Range | -65~150 | Ĉ |

BSOLUTE MAXIMUM RATINGS(Ta=25°C)

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT | |
|---------------------|--------------------------------------|-----|--------------|--|
| R _{th j-c} | Thermal Resistance, Junction to Case | 1.1 | °C /W | |





isc website: <u>www.iscsemi.com</u>



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|------------------------|--------------------------------------|---|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 30mA; I _B = 0 | 250 | | | V |
| V _{CE(sat)-1} | Collector-Emitter Saturation Voltage | I _C = 2.5A; I _B = 0.5A | | | 1.5 | V |
| V _{CE(sat)-2} | Collector-Emitter Saturation Voltage | I _C = 4A; I _B = 1.25A | | | 3.0 | V |
| V _{BE(sat)-1} | Base-Emitter Saturation Voltage | Ic= 2.5A; I _B = 0.5A | | | 1.4 | V |
| V _{BE(sat)-2} | Base-Emitter Saturation Voltage | I _C = 4A; I _B = 1.25A | | | 1.6 | V |
| І _{сво} | Collector Cutoff Current | V _{CB} = 400V; I _E = 0 | | | 1.0 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 7V; I _C = 0 | | | 1.0 | mA |
| h _{FE} | DC Current Gain | I _C = 2A; V _{CE} = 5V | 15 | | 60 | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = 0.5A; V _{CE} = 10V, f= 1.0MHz | | 10 | | MHz |

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